

CLAIMS

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What is claimed is:

1. (currently amended) A Machine for Production of Granular Silicon comprising:
- 10 a heating section located below a reacting section; where said heating section comprises one or more tubes heated by one or more heaters
- a mechanism that pulses silicon granules back and forth between the heating and reacting sections wherein the mechanism includes at least one separate injection means for injecting non silicon containing gases into the
- 15 heating section ;
- separate injection means for injecting silicon containing gases into the reacting section///
- at least one separate injection means for injecting non silicon containing gases and
- 20 a heating means to heat the non silicon containing gases above a reaction temperature .

2. (currently amended) A machine of claim 1 further including at least one additional stage connected above the reacting section and containing a second
- 25 reacting section, a heating means, and one or more gas injection means, where ~~there are multiple stages; a 1st stage comprising a heater section, a reaction section, a granule pulsing mechanism, a separate gas injection means for injecting silicon containing gases, a separate injection means for injecting non silicon containing gases and a heating means to heat the non silicon containing~~

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5 ~~gases above a reaction temperature and at least one additional stage comprising~~
~~at least a heater section, a reaction section and a gas injection means.~~

3. (currently amended) A machine of claim 1 further comprising a means
for recovering the recovery of heat from the granules by direct contact with a high
purity gas, which has carbon and oxygen containing contaminants below 1 ppmv,
10 parts per million by volume, ~~ppmw and preferably below 10ppmw~~ and which can
be selected either from a ~~1st~~first group consisting of hydrogen, helium, argon,
nitrogen and mixtures thereof, or from a 2nd second group consisting of helium,
argon, nitrogen, silicon tetrachloride, and silicon tetrabromide and mixtures
thereof. ~~but not mixtures of the 2nd group and hydrogen.~~

15 4. (currently amended) A machine of claim 1 further comprising a heat
exchanger in which one or more containment means for the silicon containing
gases are heated by hot liquid or condensing vapor maintained within a
temperature range which cannot cause decomposition of the gases; which
temperature range is typically between about 200-400°C ~~but more particularly~~
20 ~~between 200-380°C.~~

5. (currently amended) A machine of claim 1 further comprising a sieving
device, operated either continuously or in batches, by which the silicon granules
are sieved using one or more sieves manufactured from non contaminating sieve
material selected from the group consisting of single crystal silicon,
25 polycrystalline silicon, silicon oxide, silicon nitride, silicon oxynitride, silicon
carbide and mixtures thereof where the contaminants in the abradable surfaces
will typically be below 1000 ppmwt ~~and preferably below 100 ppmwt.~~

6. (currently amended) A machine of claim 1 further comprising a
feedstock recovery section; where hydrogen is injected in the heating section, a
30 silicon containing gas selected from a 4th first group, consisting of trichlorosilane
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5 dichlorosilane, tribromosilane, dibromosilane, triodosilane, diiodosilane and mixtures thereof is injected via the separate injection means for silicon containing gas in the reacting section and a silicon tetrahalide selected from a 2nd second group, consisting of silicon tetrachloride, silicon tetrabromide and silicon tetraiodide is injected after the reactor section, mixed with the reactor effluent
10 then quenched at an optimal temperature to recover hydrohalosilanes selected from the ~~afesaid~~ 1st first group, residual silicon tetrahalides selected from the 2nd second group and hydrogen.

7. (previously presented) A machine of claim 1 further comprising one or more cooled joints between external equipment and the reactor which transmit
15 hot gases or solids and which are cooled using, one or more, microchannels positioned to primarily cool the immediate area around the connection to the reactor and/or the seal area of the connection to the external equipment.

8. (currently amended) A machine of claim 1 further comprising an external flow control means for controlling flow to each of each said injection
20 means, selected from a group consisting of: a means for either direct with flow control of each said injection means done independently, or indirect by means of a means of indirect flow control by a flow distribution device or a combination of the two where some of the said injection means are ganged in groups.

9. (previously presented) A machine of claim 1 where the instantaneous
25 flow of gases into the reactor through one or more of the injection means is varied periodically and/or the distribution of flow between said injection means is adjusted to control the generation of new particles without changing the total flow averaged over 1 minute.

10. (currently amended) A machine of claim 4 where the location of the
30 one or more flow control means for the fewer silicon containing gas to one more

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5 of the separate injection means for silicon containing gas is controlled is
upstream of before the heat exchanger and an even more preferred option where
multiple separate flows containment means of the silicon containing gas are in
the same heat exchanger.

11. (previously presented) A machine of claim 2, where high purity
10 hydrogen is used for the non silicon containing gas to the first stage and silane is
injected via the separate injection means for silicon containing gas in all the
stages.

12. (currently amended) A machine of claim 2, where; high purity
hydrogen is injected in the first and subsequent stages, a silicon containing gas
15 selected from a 4th first group consisting of trichlorosilane, dichlorosilane,
tribromosilane, dibromosilane, triiodosilane, diiodosilane and mixtures thereof is
injected via the separate injection means for silicon containing gas in the 4th first
stage and further comprising a final feedstock recovery system where a silicon
tetrahalide selected from a 2nd second group consisting of silicon tetrachloride,
20 silicon tetrabromide and silicon tetraiodide is injected, mixed with the reactor
effluent then quenched at an optimal temperature to recover gases from the prior
4th first group, residual silicon tetrahalides from the prior 2nd second group and
hydrogen.

13. (currently amended) A machine of claim 1 where the heating section
25 is of smaller diameter than the reacting section above it and connected by a
tapered section, angle of said tapered section to be between 10 and 80 degrees
from the vertical and preferably between 30-60 degrees from the vertical.

14. (currently amended) A machine of claim 1 where the heaters used in
the heating sections are selected from the group consisting of resistance heaters.

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- 5 inductive RF heaters, microwave heaters, lamp heaters or lasers but are
~~preferably resistance heaters.~~

15. (previously presented) A machine of claim 6 where a cyclone is used
after the injection of the silicon tetrahalide to remove silicon dust and to provide
residence time for the mixing and reaction of the silicon tetrahalide with from the
10 reactor effluent and the silicon dust to improve the recovery of the said silicon
hydrohalosilanes and tetrahalides.

16. (currently amended) A machine of claim 1 further including a means of
supplying a silicon etching gas may be which is injected through one or more of
the injection means for the purpose of etching wall deposits from all or part of the
15 reactor, where the gas is selected from the group consisting of chlorine, bromine,
iodine, hydrogen chloride, hydrogen bromide, hydrogen iodide, a mixture of
hydrogen and silicon tetrachloride, a mixture of hydrogen and silicon
tetrabromide, a mixture of hydrogen and silicon tetraiodide and mixtures thereof.

17. (currently amended) A machine of claim 1 where the reactor is
20 supported upon a weigh cell, capable of both weighing the reactor and its
contents and of measuring the intermittent force exerted by the pulsing granules
and where the connections to and from the reactor are flexible enough to allow
the slight deflection movement required by the weigh cell, ~~said deflection to be~~
~~less than 1mm and preferably less than 0.5mm,~~ and the thermal expansion of the
25 reactor relative to the support structure, said movement ~~thermal expansion~~ to be
less than 1" (25mm) and preferably less than 1/4" (6mm).

18. (previously presented) A machine of claim 1 where all or a portion of
the non silicon containing gases are heated to a temperature below the reaction
temperature outside the heating section then heated to a temperature above the

5. reaction temperature inside the heating section prior to entry to the reacting
section.

19. (currently amended) A machine of claim 2 where at least one of the
second and subsequent the at least one additional stage heating sections
contains some residual silicon dust and/or silicon containing gases ~~from the first~~
10. ~~stage reacting section~~ that form a wall deposit:

20. (canceled)

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5 dichlorosilane, tribromosilane, dibromosilane, triodosilane, diodosilane and
 mixtures thereof is injected via the separate injection means for silicon containing
 gas in the reacting section and a silicon tetrahalide selected from a 2nd second
 group, consisting of silicon tetrachloride, silicon tetrabromide and silicon
 tetraiodide is injected after the reactor section, mixed with the reactor effluent
 10 then quenched at an optimal temperature to recover hydrohalosilanes selected
 from the aforesaid 1st first group, residual silicon tetrahalides selected from the
2nd second group and hydrogen.

7. (previously presented) A machine of claim 1 further comprising one or
 more cooled joints between external equipment and the reactor which transmit
 15 hot gases or solids and which are cooled using, one or more, microchannels
 positioned to primarily cool the immediate area around the connection to the
 reactor and/or the seal area of the connection to the external equipment.

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 20 means, selected from a group consisting of: a means for either direct with flow
control of each said injection means done independently, or indirect by means of
a means of indirect flow control by a flow distribution device or a combination of
 the two where some of the said injection means are ganged in groups.

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 25 flow of gases into the reactor through one or more of the injection means is
 varied periodically and/or the distribution of flow between said injection means is
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10. (currently amended) A machine of claim 4 where the location of the
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tribromosilane, dibromosilane, triiodosilane, diiodosilane and mixtures thereof is
injected via the separate injection means for silicon containing gas in the 1st first *
stage and further comprising a final feedstock recovery system where a silicon
tetrahalide selected from a 2nd second group consisting of silicon tetrachloride,
20 silicon tetrabromide and silicon tetraiodide is injected, mixed with the reactor
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5 inductive RF heaters, microwave heaters, lamp heaters or lasers but are preferably resistance heaters.

15. (previously presented) A machine of claim 6 where a cyclone is used after the injection of the silicon tetrahalide to remove silicon dust and to provide residence time for the mixing and reaction of the silicon tetrahalide with from the reactor effluent and the silicon dust to improve the recovery of the said silicon hydrohalosilanes and tetrahalides.

16. (currently amended) A machine of claim 1 further including a means of supplying a silicon etching gas may be which is injected through one or more of the injection means for the purpose of etching wall deposits from all or part of the reactor, where the gas is selected from the group consisting of chlorine, bromine, iodine, hydrogen chloride, hydrogen bromide, hydrogen iodide, a mixture of hydrogen and silicon tetrachloride, a mixture of hydrogen and silicon tetrabromide, a mixture of hydrogen and silicon tetraiodide and mixtures thereof.

17. (currently amended) A machine of claim 1 where the reactor is supported upon a weigh cell, capable of both weighing the reactor and its contents and of measuring the intermittent force exerted by the pulsing granules and where the connections to and from the reactor are flexible enough to allow the slight deflection movement required by the weigh cell, said deflection to be less than 1mm and preferably less than 0.5mm, and the thermal expansion of the reactor relative to the support structure, said movement thermal expansion to be less than 1" (25mm) and preferably less than 1/4" (6mm).

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A Machine for Production of Granular Silicon

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U.S. Patent Application of:

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Stephen Michael Lord

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5 Related Applications

Application Number 09/507,154

Filing Date 02/18/2000

GRP Art Unit 1754

Inventor: Stephen M. Lord

10 Title: Method for Improving the Efficiency of A Silicon Purification Process

Application Number 09/589563

Filing Date 06/06/00

GRP Art Unit 1754

Inventor: Stephen M. Lord

15 Title : Methods for Heating a Fluidized Bed Silicon Deposition Apparatus

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